



60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C (Note 9)
60V	3.1mΩ @ V _G S = 10V	100A

Description and Applications

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

- DC Motor Control
- Synchronous Rectification
- DC/DC Converters

Features

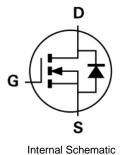
- Rated to +175°C Ideal for High Ambient Temperature **Environments**
- 100% Unclamped Inductive Switching (UIS) Test in Production -Ensures More Reliable And Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_q Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMTH6004SPSQ)

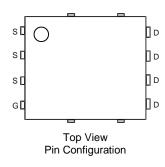
Mechanical Data

- Case: PowerDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

Site1:





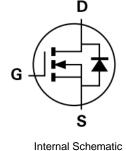


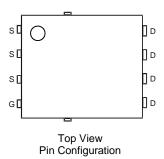
Site2:

PowerDI5060-8 (SWP) (Type UX)



Bottom View





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Ordering Information (Note 4)

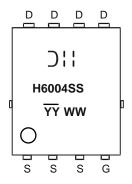
Part Number	Case	Packaging
DMTH6004SPS-13	PowerDI5060-8	2,500 / Tape & Reel
DMTH6004SPS-13	PowerDI5060-8 (SWP) (Type UX)	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





⊃¦¦= Manufacturer's Marking H6004SS = Product Type Marking Code YYWW or YYWW = Date Code Marking YY or \overline{YY} = Year (ex: 20 = 2020) WW = Week (01 to 53)



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note 5) Steady State $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		Ι _D	25 21	А	
Continuous Drain Current (Notes 6 & 9) $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$			ΙD	100 100	Α
Maximum Continuous Body Diode Forward Current (Notes 6 & 9)			Is	100	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	400	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	400	Α
Avalanche Current, L = 0.2mH			las	45	Α
Avalanche Energy, L = 0.2mH			Eas	200	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	3.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	47	°C/W
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	P _D	167	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	0.9	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

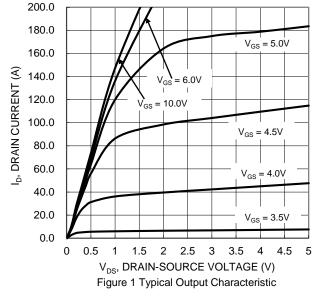
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	1	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS			1	μΑ	V _{DS} = 48V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	2	_	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS} (ON)	1	2.5	3.1	mΩ	$V_{GS} = 10V, I_{D} = 50A$	
Diode Forward Voltage	VsD		0.9	1.2	V	V _G S = 0V, I _S = 20A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		4556	_		V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss		1383	_	pF		
Reverse Transfer Capacitance	Crss		105.2	_			
Gate Resistance	Rg		0.66	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	1	95.4	_		\/ 20\/ I- 00A	
Gate-Source Charge	Qgs		21.6	_	nC	V _{DD} = 30V, I _D = 90A, V _{GS} = 10V	
Gate-Drain Charge	Q_{gd}	1	20.4	_			
Turn-On Delay Time	td(ON)		13.2	_			
Turn-On Rise Time	t _R	_	11.7	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $I_D = 90A, R_G = 3.5\Omega$	
Turn-Off Delay Time	tD(OFF)	1	31	_	115		
Turn-Off Fall Time	tF	1	12	_			
Body Diode Reverse Recovery Time	trr	_	50.5	_	ns	1 500 1:/14 1000/	
Body Diode Reverse Recovery Charge	Q _{RR}		80.8	_	nC	I _F = 50A, di/dt = 100A/μs	

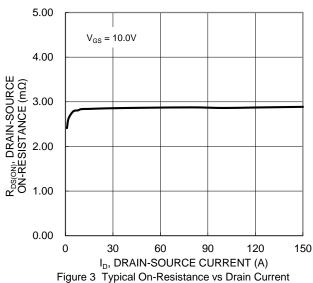
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

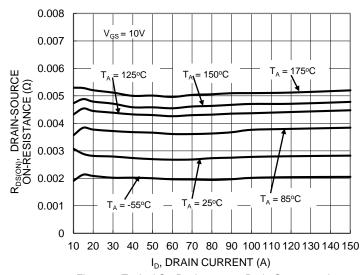
- 6. Thermal resistance from junction to soldering point (on the exposed drain pad).7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.
- 9. Package limited.

DMTH6004SPS Document number: DS37353 Rev. 7 - 2









and Gate Voltage

Figure 5 Typical On-Resistance vs Drain Current and Temperature

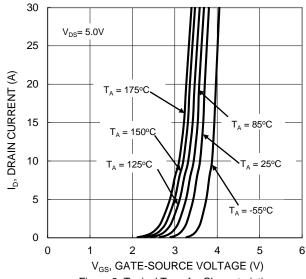
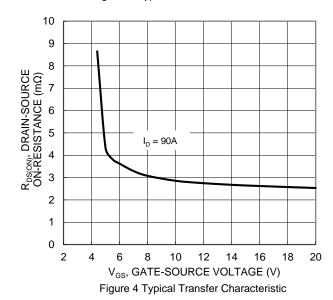


Figure 2 Typical Transfer Characteristic



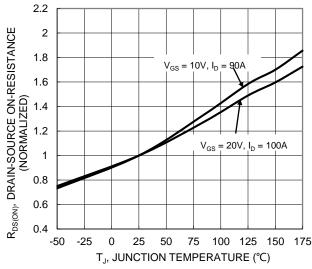


Figure 6 On-Resistance Variation with Temperature



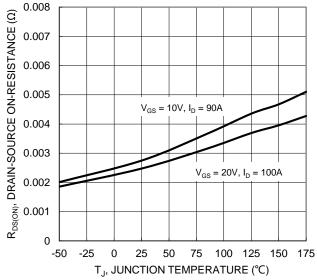
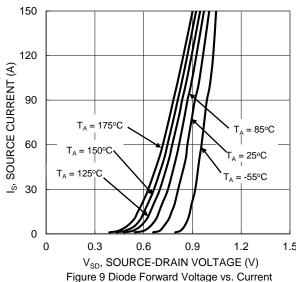
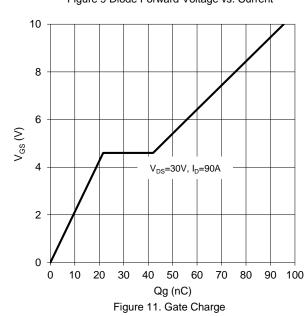


Figure 7 On-Resistance Variation with Temperature





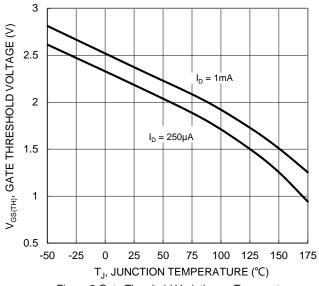
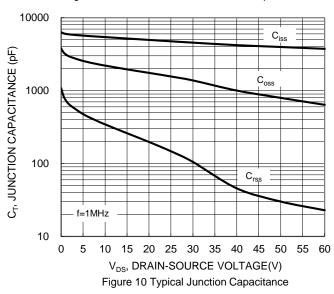


Figure 8 Gate Threshold Variation vs Temperature



1000 R_{DS(ON)} Limited 100 ID, DRAIN CURRENT (A) P_W =10ms 10 P_W =100μs $T_{J(Max)} = 175^{\circ}C$ T_C = 25°C Single Pulse $P_W = 10 \mu s$ **DUT** on Infinite Heatsink V_{GS}= 10V 0.1 100 ${
m V_{DS}},{
m DRAIN} ext{-SOURCE VOLTAGE}$ (V) Figure 12. SOA, Safe Operation Area



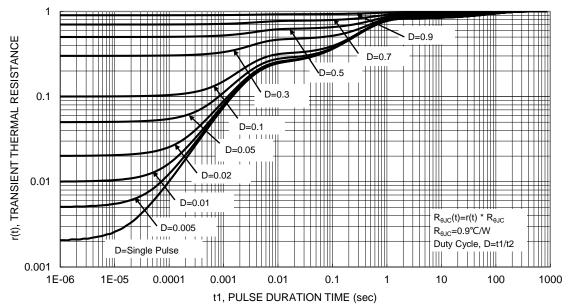


Figure 13. Transient Thermal Resistance

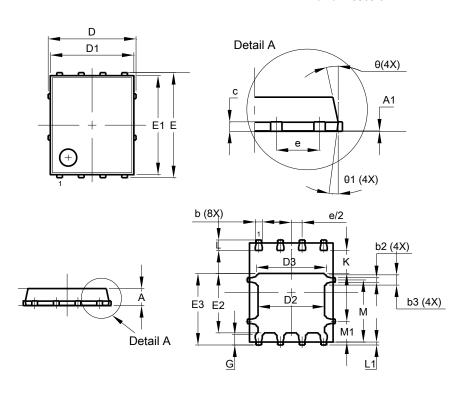


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site1:

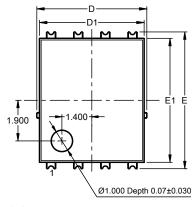
PowerDI5060-8

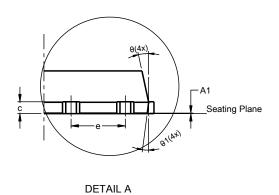


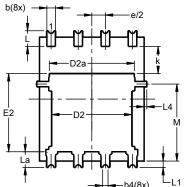
	D	15000		
PowerDI5060-8				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0.00	0.05	-	
b	0.33	0.51	0.41	
b2	0.200	0.350	0.273	
b3	0.40	0.80	0.60	
С	0.230	0.330	0.277	
D	5	.15 BS	0	
D1	4.70	5.10	4.90	
D2	3.70	4.10	3.90	
D3	3.90	4.30	4.10	
Е	6	.15 BS	2	
E1	5.60	6.00	5.80	
E2	3.28	3.68	3.48	
E3	3.99	4.39	4.19	
е	1	.27 BS0)	
G	0.51	0.71	0.61	
K	0.51	-	-	
L	0.51	0.71	0.61	
L1	0.100	0.200	0.175	
М	3.235	4.035	3.635	
M1	1.00	1.40	1.21	
Θ	10°	12°	11°	
Θ1	6°	8°	7°	
All Dimensions in mm				

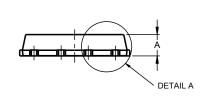
Site2:

PowerDI5060-8 (SWP) (Type UX)









PowerDI5060-8 (SWP) (Type UX)			
Dim	Min	Max	Тур
Α	0.90	1.10	1.00
A1	0	0.05	
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	().25REF	=
С	0.230	0.330	0.277
D	5	.15 BS0	2
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
Е	6	.40 BS0	2
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
е	1	.27BSC)
k	1.05		
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

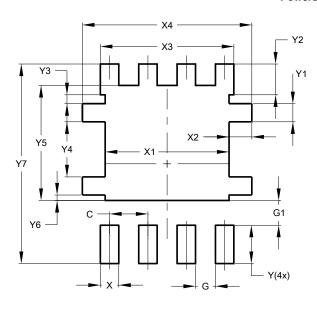


Suggested Pad Layout

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Site1:

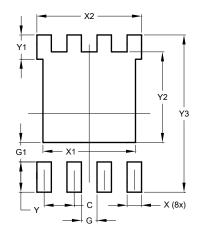
PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Υ	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site2:

PowerDI5060-8 (SWP) (Type UX)



Dimensions	value
Dimensions	(in mm)
С	1.270
G	0.660
G1	0.820
Χ	0.610
X1	4.100
X2	4.420
Υ	1.270
Y1	1.020
Y2	3.810
Y3	6.610



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